/ Descriptions

TO-263 PNP Silicon PNP transistor in a TO-263 Plastic Package.

/ Features

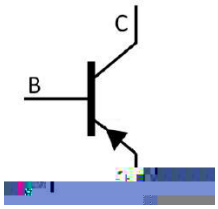
- - MJE15036B

High DC current gain, High V_{CEO}, High f_T. Complementary pair with MJE15036B.

/ Applications

Designed for us as high-frequency drivers in audio amplifiers.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 4 Collector PIN 3 Emitter

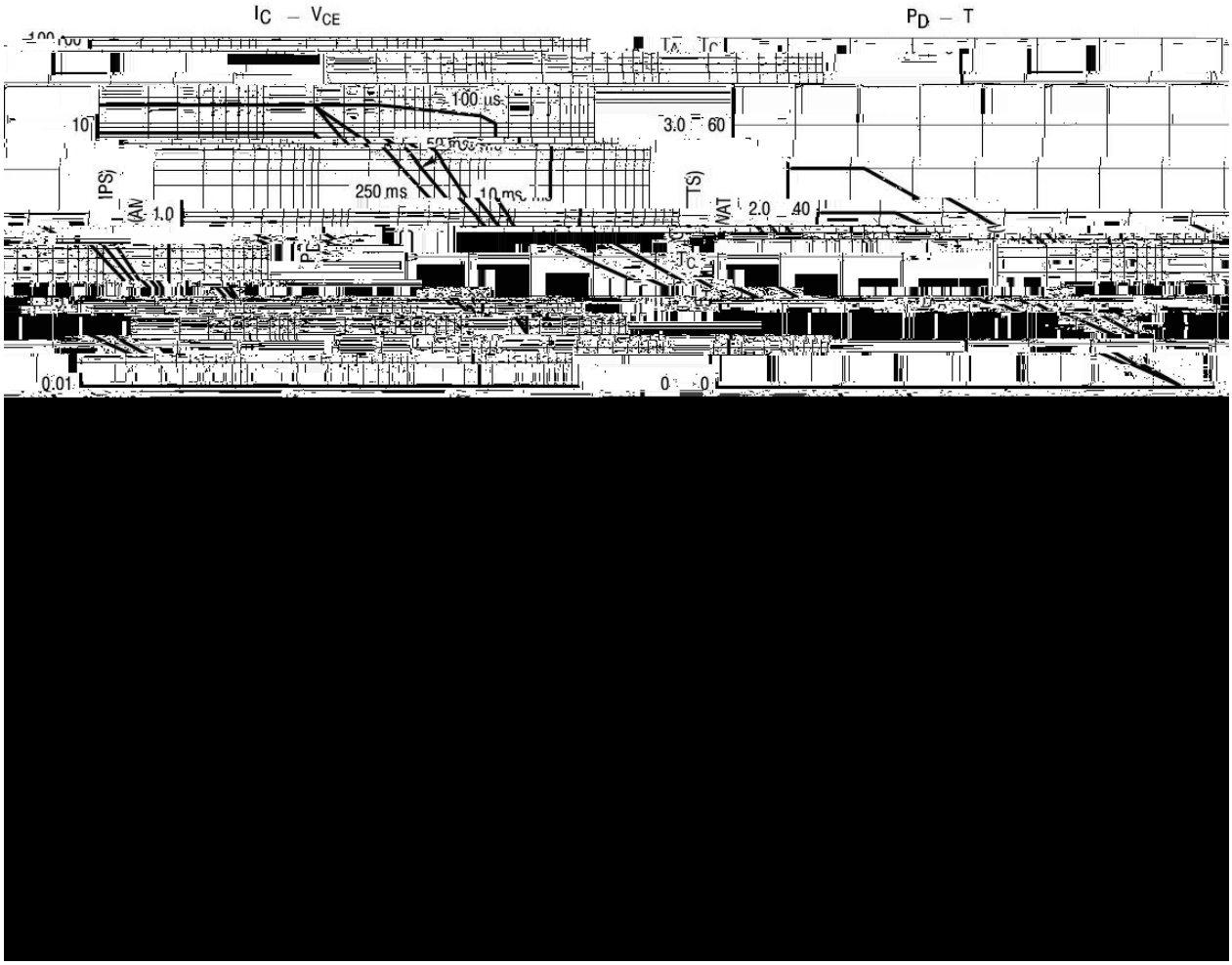
/ h_{FE} Classifications & Marking

See Marking Instructions.

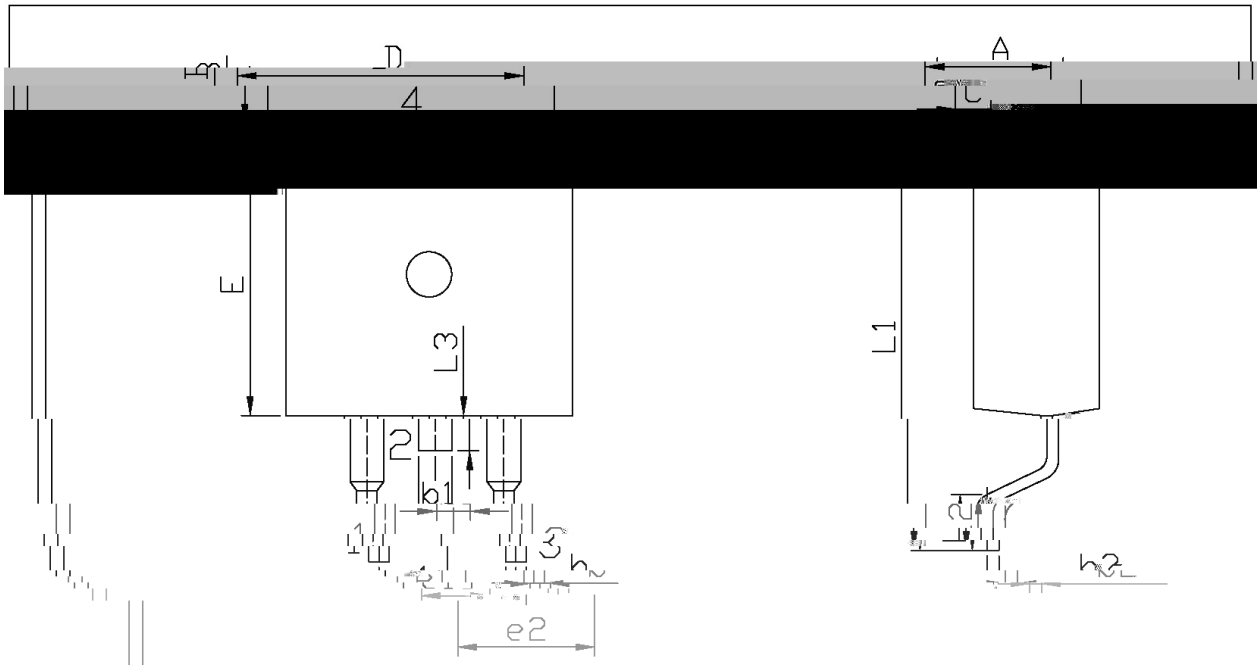
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-250	V
Collector to Emitter Voltage	V_{CEO}	-250	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-8	A
Base current	I_B	-2	A
Total power dissipation	P_D	2	W
Total power dissipation	P_D(Tc=25)	50	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	
Thermal Resistance Junction-case	$R_{\theta JC}$	2.5	/W
Thermal Resistance Junction-ambient	$R_{\theta JA}$	62.5	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage*	*V_{CEO}	I_C=-10mA I_B=0	250			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-250V I_E=0			-1	μA

/ Electrical Characteristic Curve



/ Package Dimensions

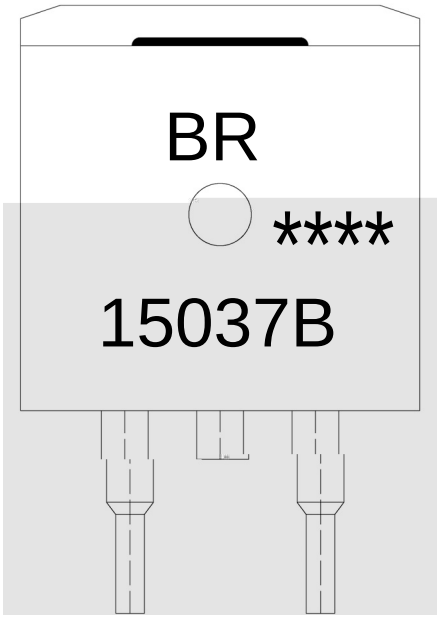


单位：mm

Dimensions In Millimeters		Dimensions In Millimeters	
Min	Max	Min	Max
A	4.30	4.70	L	9.00	9.40
B	1.00	1.40	e1	2.34	2.74

TO-263

/ Marking Instructions



BR

15037B

****

Note:

BR:	Company Code
15037B:	Product Type.
****:	Lot No. Code, code change with Lot No.